


APPLICATION	REVISIONS		
USED ON	DESCRIPTION	DATE	APPRVD
EMD1710	ENGR CHANGE ORDER ECO# 2002	9.28.16	N

ECLIPSE MICROWAVE, INC **PROPRIETARY INFORMATION**

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ALL SHEETS ARE THE SAME REVISION UNLESS OTHERWISE SPECIFIED	ALL TEXT AND GRAPHICS COMPUTER GENERATED; DO NOT REVISE MANUALLY UNLESS OTHERWISE SPECIFIED	COMPANY PROCEDURE			
<ul style="list-style-type: none"> Interpret drawing per ASME Y14.100M-1998 Dim & Tol IAW ASME Y14.5M-1994 Dimensions are in inches or inches/metric Dimensional limits apply after processes Tolerances: Angles $\pm 2^\circ$ 3 pl decimals $\pm .010$ 2 pl decimals $\pm .020$ Drilled hole tolerances shall be IAW AND10387 Remove all burrs & sharp edges .010 R max Surface finish: .63V Concentricity machined dia .002 T1M Machine tool mismatch: .003 max 	SIGNATURES	DATE			
	DRW BY: <i>mnw</i>	<i>9/29/16</i>		TITLE SPECIFICATION	
	MFR ENGR:				
	ENGR: <i>N</i>	<i>9.28.16</i>			
	QA APPR: <i>mnw</i>	<i>9/29/16</i>	SIZE A	CAGE CODE 1XDA1	DOCUMENT NO. 730005
PROCESS OWNER: SALES			SHEET Page 1 of 6		

GaAs PHEMT MMIC
Driver Amplifier, QFN4mm

2.0 TO 20.0 GHz

EMD1710

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730005

REV.:

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PROCESS OWNER:

SALES

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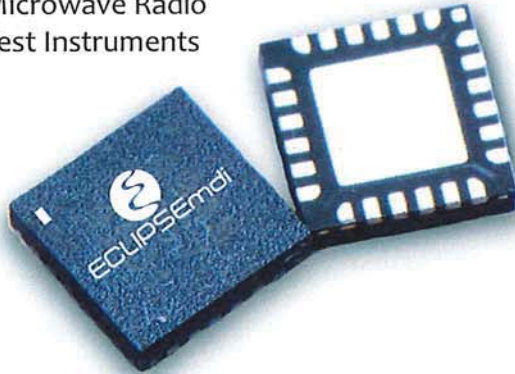
GaAs PHEMT MMIC
 Low Noise Distributed Amplifier
 QFN4mm
 2 to 20 GHz



EMD1710

Typical Applications

- †† General Purpose Application
- †† Commercial and Industrial Application
- †† VSAT
- †† Microwave Radio
- †† Test Instruments



FEATURES

- ◊ 2.0 dB Noise Figure @ 10 GHz
- ◊ 12.5 dB Gain @ 10 GHz
- ◊ +18.5 dBm P1dB Output Power @ 10 GHz
- ◊ +5V @ 83 mA typical supply voltage
- ◊ Low Cost QFN 4mm leadless RoHS Compliant package
- ◊ Hermetically Sealed
- ◊ Die available upon request

Product Description

Eclipse Microdevices EMD1710 is a GaAs MMIC PHEMT Distributed General Purpose Low Noise Amplifier. This LNA has a small signal gain of 12 dB with noise figure less than 2.0 dB at 10 GHz. This device is ideal for applications that requires a typical P1dB output power of +18 dBm up to 12 GHz, while requiring only 83mA from a + 5 Volt supply. The EMD1710 comes in a small RoHS compliant 4mm QFN leadless package and this package has excellent RF and thermal properties ideal for commercial and industrial applications.

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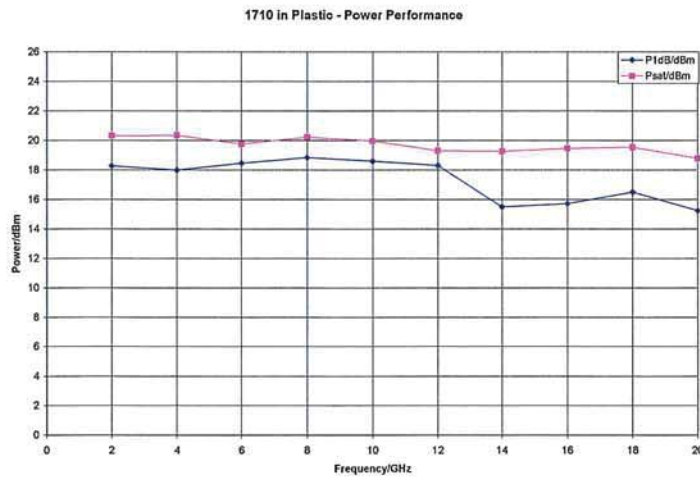
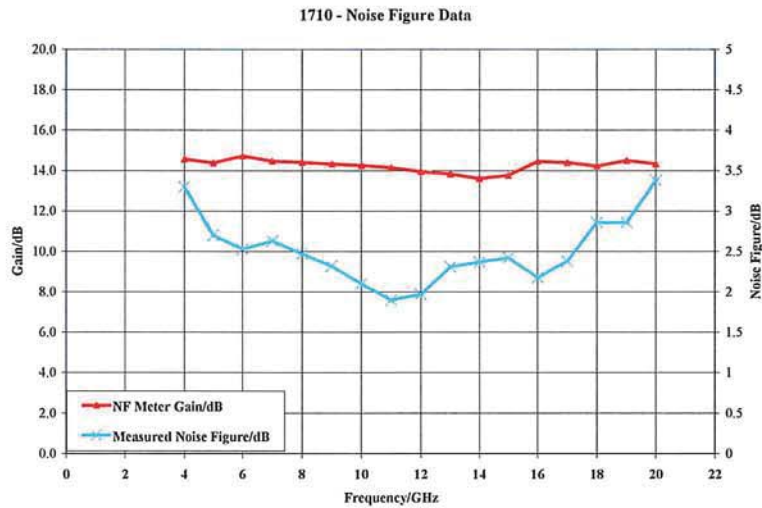
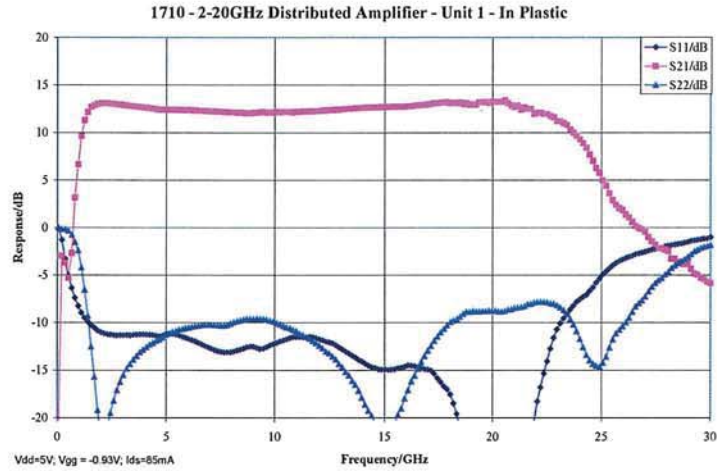
ELECTRICAL SPECIFICATION @ +25 °C, Vdd=5V, Ids=83mA

Parameters	SPECIFICATION				
	FREQ. (GHz)	MIN	TYPICAL	MAX	Units
Gain	2.0	12.5	13.1		dB
	8.0	11.5	12.1		dB
	14.0	11.5	12.6		dB
	20.0	12.8	13.2		dB
Gain Flatness	2.0 to 10.0		±0.20	±0.40	dB
	10.0 to 20.0		±0.25	±0.40	dB
Gain Variation Over Temperature				0.02	dB/°C
Noise Figure	2.0		4.4		dB
	8.0		2.5		dB
	14.0		2.4		dB
	20.0		3.4		dB
Input Return Loss(S11)			11		dB
Output Return Loss(S22)			10		dB
1 dB Compression Point(P1dB)	2.0		18.3		dBm
	8.0		18.9		dBm
	14.0		15.5		dBm
	20.0		15.2		dBm
Saturated Output Power(Psat)	2.0		20.5		dBm
	8.0		20.5		dBm
	14.0		19.5		dBm
	20.0		19.0		dBm
Third-Order Output Intercept Point			28		dBm

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 QFN4mm
 2 to 20 GHz



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GaAs PHEMT MMIC

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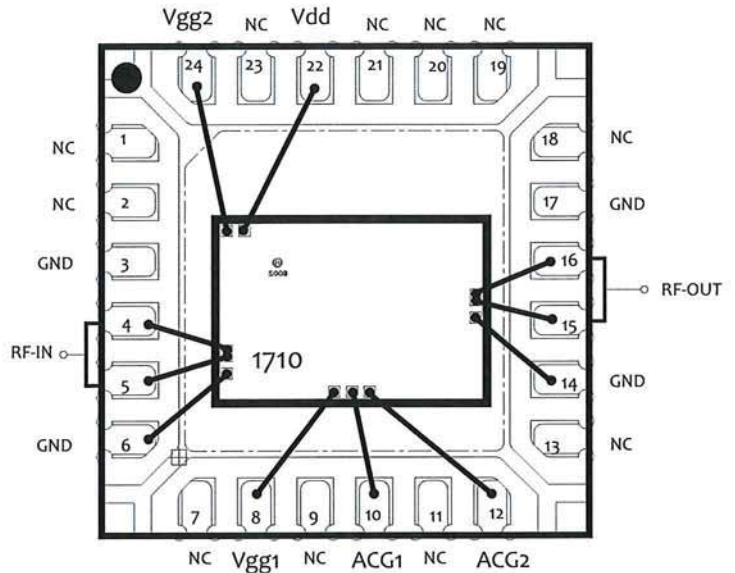


EMD1710

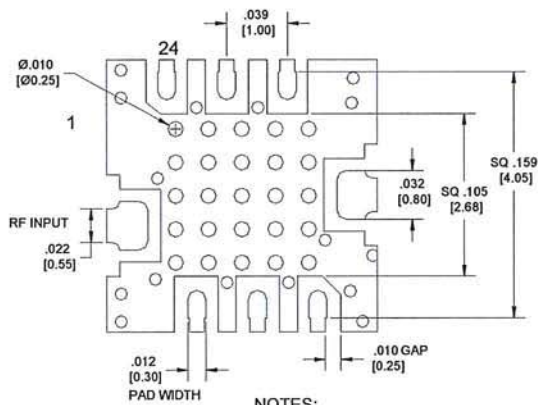
Absolute Maximum Rating

RF Input Power: +18 dBm
 Drain Voltage(Vdd): +8.0 VDC
 Gate Voltage(Vgg): -2 to 0 Volts
 Max Tj 85°C: +110°C
 Storage Temp: -55 to +150°C
 Operating Temp: -40 to +85°C

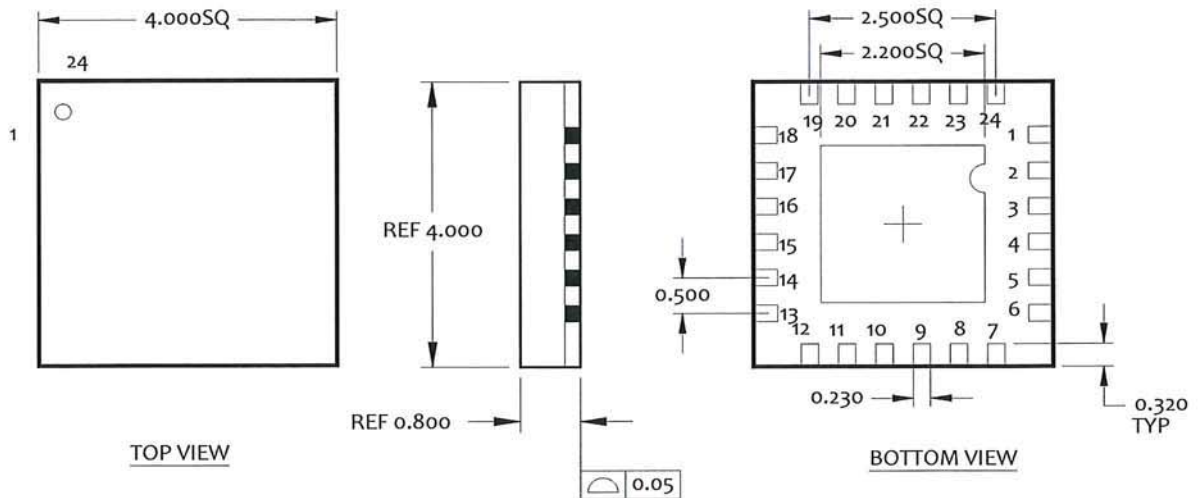
Functional Block Diagram



RECOMMENDED PCB LAYOUT



NOTES:
 1. MATERIAL: ROGERS 4350, 10 MIL THICK
 2. DIMENSIONS ARE IN INCHES[MM]

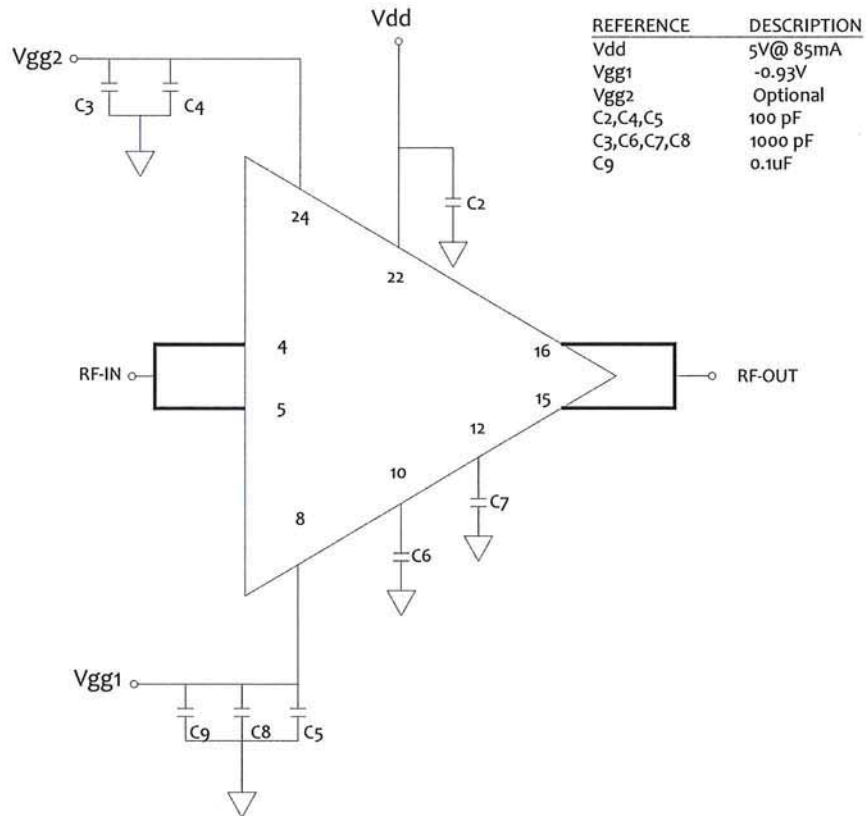


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Application Circuit



NOTE: Adjust Vgg1 to between -2 to 0 volts to achieve $I_{ds}=85$ mA typical

AMPLIFIERS || GaAs MMIC PHEMT